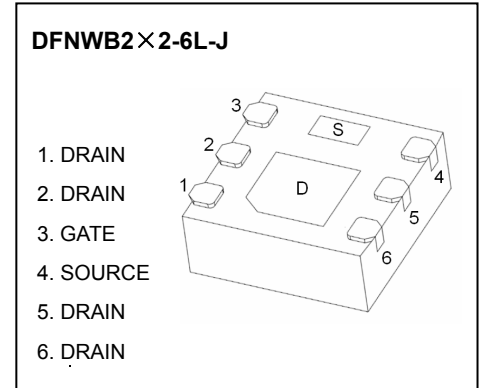


CJMP3009 P-Channel Enhancement Mode Field Effect Transistor

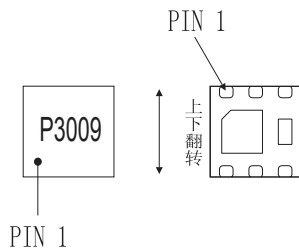
$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-30V	28mΩ@-4.5V	-9A
	40mΩ@-2.5V	



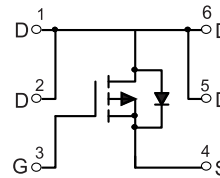
General Description

The CJMP3009 uses advanced trench technology to provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications.

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-9	A
Power Dissipation	P_D	750	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	165	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

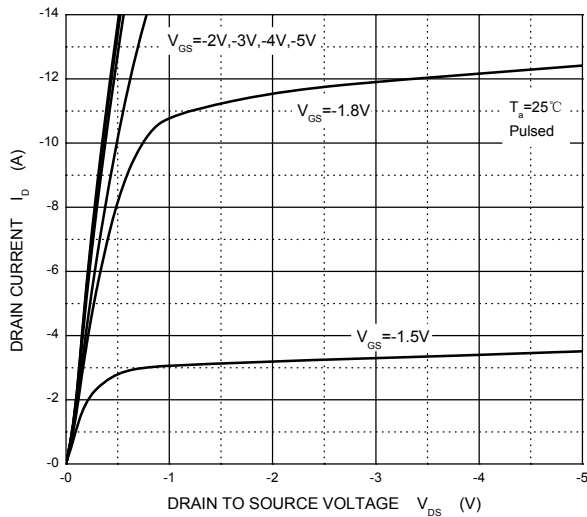
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -9A$		20	28	m Ω
		$V_{GS} = -2.5V, I_D = -6A$		27	40	m Ω
Forward transconductance (note 1)	g_{FS}	$V_{DS} = -5V, I_D = -9A$		24		S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.6	-0.9	-1.5	V
Diode forward voltage (note 1)	V_{SD}	$I_S = -2A, V_{GS} = 0V$			-1.2	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		780		pF
Output capacitance	C_{oss}			150		pF
Reverse transfer capacitance	C_{rss}			98		pF
Switching Characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -4.5V, V_{DS} = -6V,$ $I_D = -9A, R_{GEN} = 6\Omega$		11		ns
Turn-on rise time	t_r			8		ns
Turn-off delay time	$t_{d(off)}$			28.5		ns
Turn-off fall time	t_f			10.5		ns
Total gate charge	Q_g	$V_{GS} = -4.5V, V_{DS} = -6V,$ $I_D = -9A$		13.8		nC
TGate-source charge	Q_{gs}			2.5		nC
TGate-drain charge	Q_{gd}			3.3		nC

Notes:

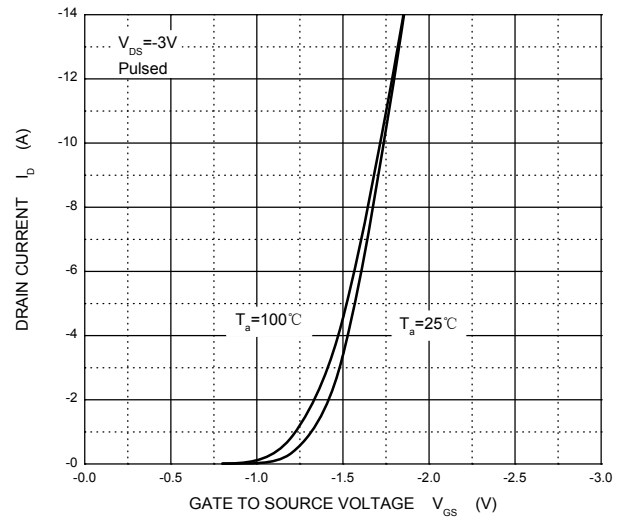
1. Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. These parameters have no way to verify.

Typical Characteristics

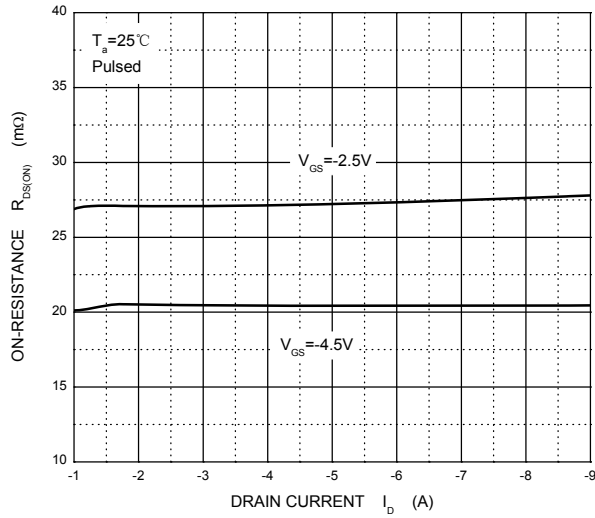
Output Characteristics



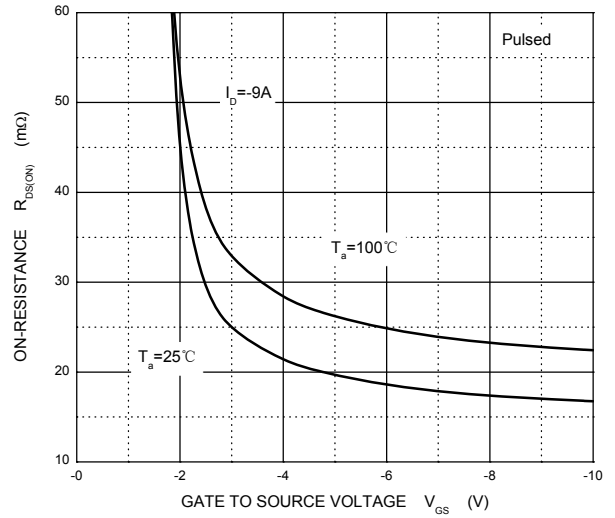
Transfer Characteristics



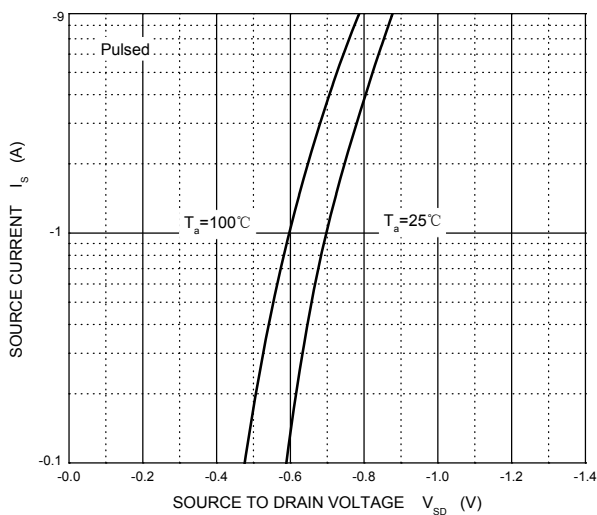
$R_{DS(ON)}$ — I_D



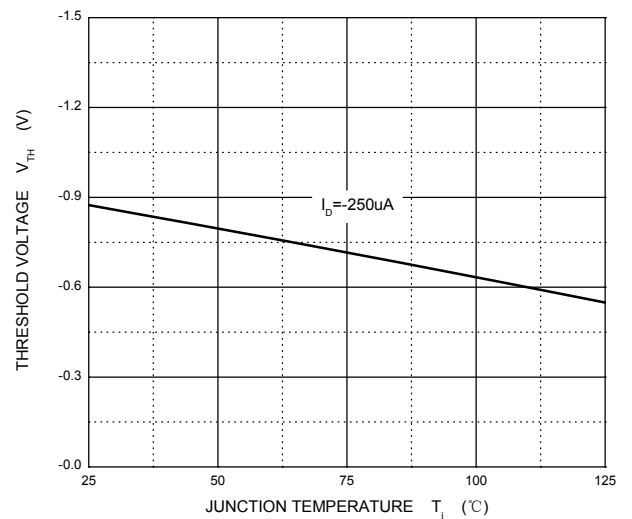
$R_{DS(ON)}$ — V_{GS}



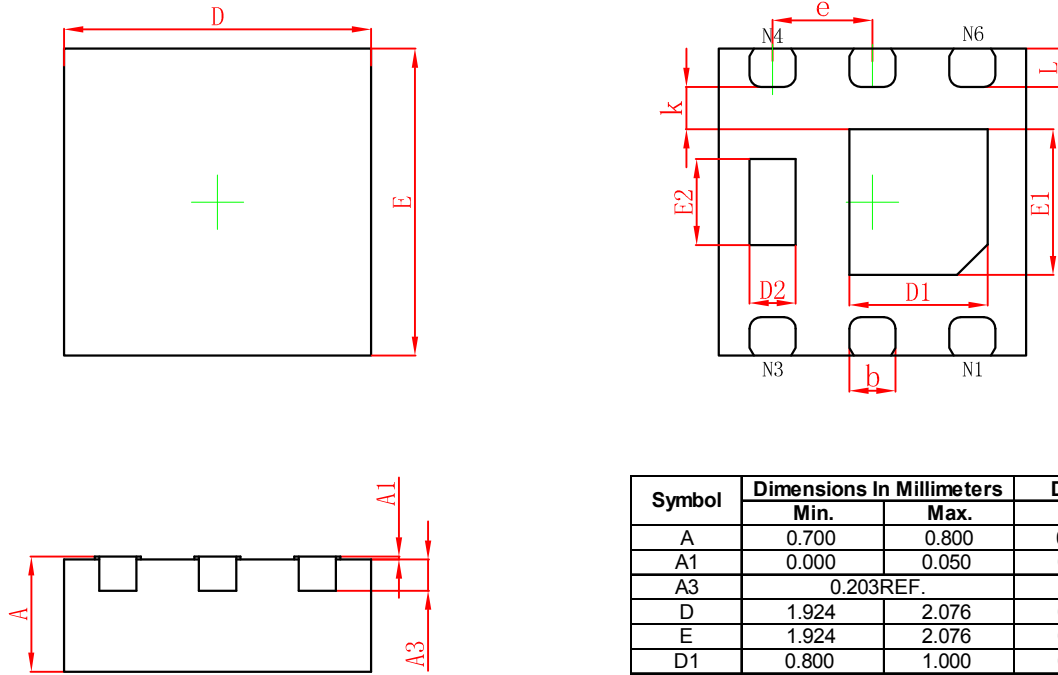
I_S — V_{SD}



Threshold Voltage

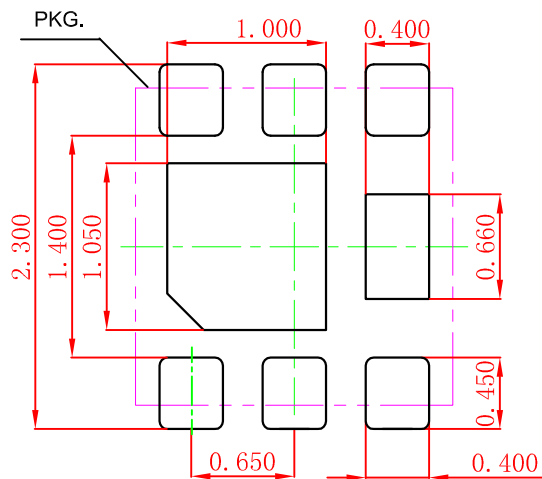


DFNWB2X2-6L-J Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.032
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

DFNWB2X2-6L-J Suggested Pad Layout



Note:

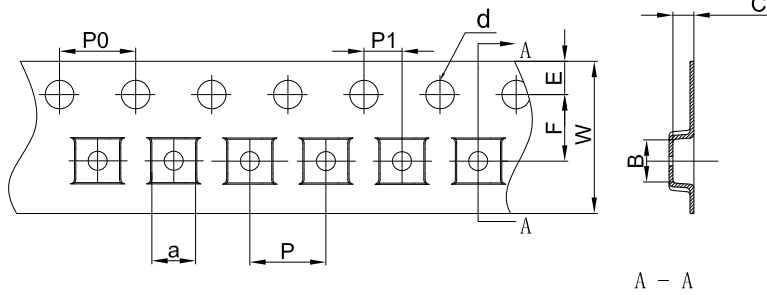
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.050\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

DFNWB2X2-6L Tape and Reel

DFNWB2×2-6L Embossed Carrier Tape



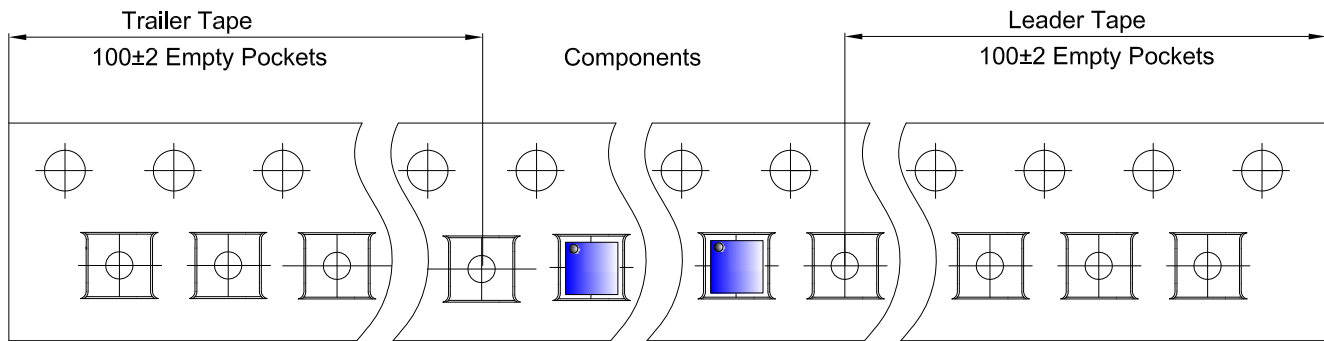
Packaging Description:

DFNWB2×2-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

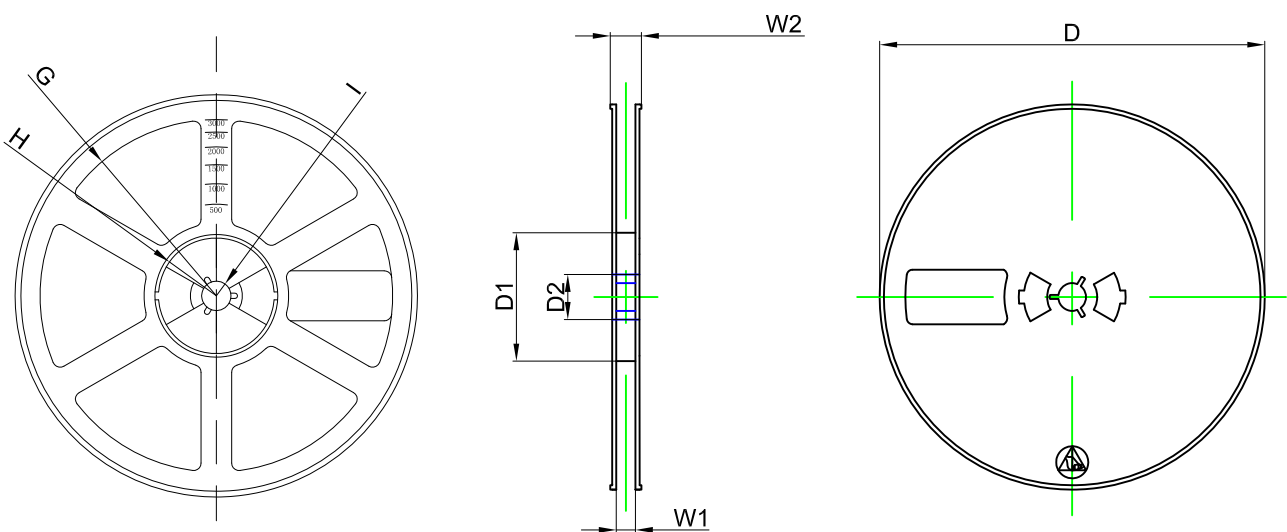
Dimensions are in millimeter

Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

DFNWB2×2-6L Tape Leader and Trailer



DFNWB2×2-6L Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

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[IPS60R360PFD7SAKMA1](#) [IPS60R600PFD7SAKMA1](#)